Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.15	V
I_L	I_G =1.2I_{GT}	-	MAX.	70	mA
				80	
I_H	I_T =500mA		MAX.	60	mA
dV/dt	V_D=800V Gate Open T_j =125		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125		MIN.	15	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	7	μs
t_{off}				50	

STATIC CHARACTERISTICS

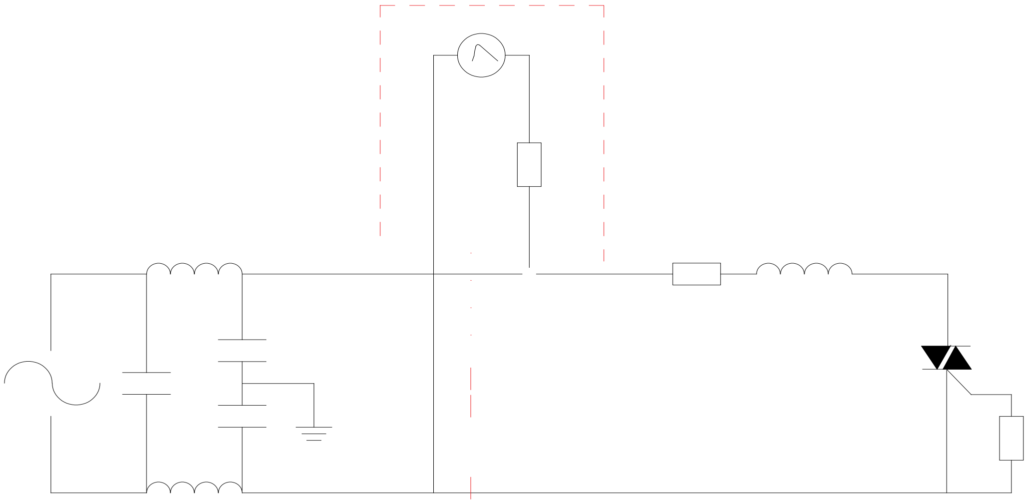
Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =42A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.73	V
R_D	Dynamic resistance	T_j=125	25	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	10	μA
I_{RRM}		T_j=125	4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

FIG.1: Maximum power dissipation

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA [illegible]